2SC3611

Silicon NPN epitaxial planar type

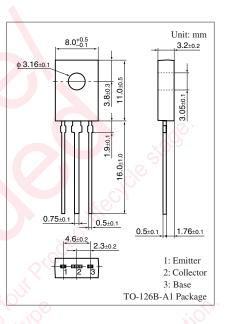
For video amplifier

Features

- \bullet High transition frequency $f_{\rm T}$
- \bullet Small collector output capacitance (Common base, input open circuited) C_{ob}
- Wide current range
- TO-126B package which requires no insulation plate for installation to the heat sink

Absolute Maximum Ratings $T_a = 25^{\circ}C$							
Parameter	Symbol	Rating	Unit				
Collector-base voltage (Emitter open)	V _{CBO}	110	V				
Collector-emitter voltage (Resistor between B and E)	V _{CER}	100	V				
Collector-emitter voltage (Base open)	V _{CEO}	50	V				
Emitter-base voltage (Collector open)	V _{EBO}	3.5	v				
Collector current	I _C	150	mA				
Peak collector current	I _{CP}	300	mA				
Collector power dissipation	P _C	1.2	W				
		4.0 *					
Junction temperature	Tj	150	°C				
Storage temperature	T _{stg}	-55 to +150	°C ()				

Absolute Maximum Ratings $T_a = 25^{\circ}C$



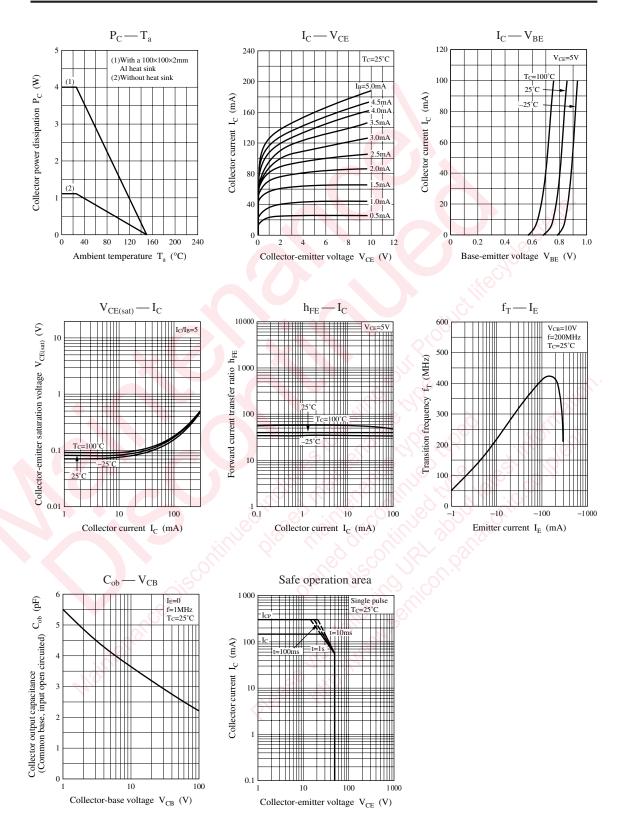
Note) *: With a $100 \times 100 \times 2$ mm Al heat sink

Electrical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	V _{CBO}	$I_{\rm C} = 100 \ \mu {\rm A}, I_{\rm E} = 0$	110			V
Collector-emitter voltage (Resistor between B and E)	V _{CER}	$I_{C} = 500 \ \mu A, R_{BE} = 470 \ \Omega$	100			V
Collector-emitter voltage (Base open)	V _{CEO}	$I_{\rm C} = 1 {\rm mA}, I_{\rm B} = 0$	50			V
Emitter-base voltage (Collector open)	V _{EBO}	$I_{\rm E} = 100 \ \mu A, \ I_{\rm C} = 0$	3.5			V
Collector-emitter cutoff current (Base open)	I _{CEO}	$V_{CE} = 35 \text{ V}, I_{B} = 0$			10	μΑ
Forward current transfer ratio	h _{FE}	$V_{CE} = 5 \text{ V}, \text{ I}_{C} = 100 \text{ mA}$	20			_
Collector-emitter saturation voltage	V _{CE(sat)}	$I_{\rm C} = 150 \text{ mA}, I_{\rm B} = 15 \text{ mA}$			0.5	V
Transition frequency	f _{T1}	$V_{CB} = 10 \text{ V}, I_E = -10 \text{ mA}, f = 200 \text{ MHz}$		300		MHz
	f _{T2}	$V_{CB} = 10 \text{ V}, I_E = -110 \text{ mA}, f = 200 \text{ MHz}$		350		
Collector output capacitance (Common base, input open circuited)	C _{ob}	$V_{CB} = 30 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		3		pF

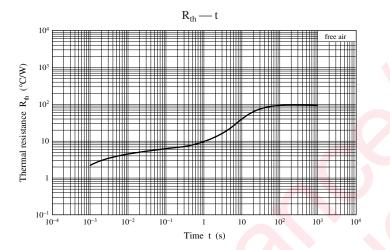
Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

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